Low-Voltage CMOS Unbuffered Hex Inverter

With 5 V-Tolerant Inputs

The MC74LCXU04 is a high performance unbuffered hex inverter operating from a 2.3 to 3.6 V supply. (High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance.) A VI specification of 5.5 V allows MC74LCXU04 inputs to be safely driven from 5 V devices.

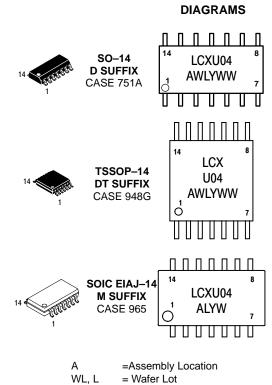
- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- Near Zero Static Supply Current (10 µA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



ON Semiconductor

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MARKING



ORDERING INFORMATION

= Year

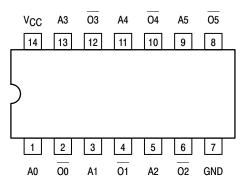
= Work Week

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WW, W

Device	Package	Shipping
MC74LCXU04D	SO-14	55 Units/Rail
MC74LCXU04DR2	SO-14	2500 Units/Reel
MC74LCXU04DT	TSSOP-14	96 Units/Rail
MC74LCXU04DTR2	TSSOP-14	2500 Units/Reel
MC74LCXU04M	SOIC EIAJ–14	50 Units/Rail
MC74LCXU04MEL	SOIC EIAJ–14	2000 Units/Reel

PINOUT: 14-LEAD (Top View)



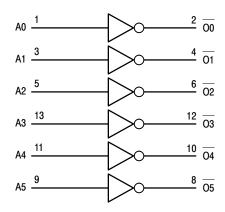
PIN NAMES

Pins	Function
An	Data Inputs
On	Outputs

TRUTH TABLE

An	On
L	H
H	L

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
VCC	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{I} \le +7.0$		V
VO	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State. (Note 1.)	V
Iк	DC Input Diode Current	-50	V _I < GND	mA
lок	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
lO	DC Output Source/Sink Current	±50		mA
ICC	DC Supply Current Per Supply Pin	±100		mA
IGND	DC Ground Current Per Ground Pin	±100		mA
TSTG	Storage Temperature Range	-65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. IO absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Paramet	er	Min	Тур	Max	Unit
VCC	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
VO	Output Voltage	(HIGH or LOW State)	0		VCC	V
IOH	HIGH Level Output Current	$V_{CC} = 3.0V - 3.6V$ $V_{CC} = 2.7V - 3.0V$ $V_{CC} = 2.3V - 2.7V$			- 18 - 12 - 8	mA
IOL	LOW Level Output Current	$V_{CC} = 3.0V - 3.6V$ $V_{CC} = 2.7V - 3.0V$ $V_{CC} = 2.3V - 2.7V$			+ 16 + 12 + 8	mA
т _А	Operating Free–Air Temperature		-40		+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate, V_{IN} V _{CC} = 3.0V	from 0.8V to 2.0V,	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

	Characteristic		T _A = −40°C		
Symbol		Condition	Min	Max	Unit
VIH	HIGH Level Input Voltage (Note 2.)	V _{CC} =2.3 V	1.7		V
		V _{CC} =2.7 V	2.1		
		V _{CC} =3.0 V	2.2		
		V _{CC} =3.6 V	2.7		
VIL	LOW Level Input Voltage (Note 2.)	V _{CC} =2.3 V		0.55	V
		V _{CC} =2.7 V		0.55	
		V _{CC} =3.0 V		0.55	
		V _{CC} =3.6V		0.55	
VOH	HIGH Level Output Voltage	2.3 V \leq V_CC \leq 3.6 V; I_OL = 100 μA	V _{CC} – 0.2		V
		$V_{CC} = 2.3 \text{ V}; \text{ I}_{OH} = -8 \text{ mA}$	1.8		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -18 \text{ mA}$	2.4		
VOL	LOW Level Output Voltage	2.3 V \leq V_CC \leq 3.6 V; I_OL = 100 μA		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		$V_{CC} = 2.7 \text{ V}; \text{ I}_{OL} = 12 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OL} = 16 \text{ mA}$		0.5	
lj	Input Leakage Current	$2.3 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}; 0 \text{ V} \leq \text{V}_{I} \leq 5.5 \text{ V}$		±5.0	μΑ
loz	3-State Output Current	$\begin{array}{l} 2.3 \leq V_{CC} \leq 3.6 \text{ V}; \mbox{ OV} \leq V_O \leq 5.5 \text{ V}; \\ V_I = V_{IH} \mbox{ or } V_{IL} \end{array}$		±5.0	μA
IOFF	Power-Off Leakage Current	V_{CC} = 0 V; VI or V _O = 5.5 V		10	μΑ
ICC	Quiescent Supply Current	2.3 \leq V_{CC} \leq 3.6 V; V_I = GND or V_{CC}		10	μΑ
		$2.3 \leq V_{CC} \leq 3.6$ V; $3.6 \leq V_{I}$ or $V_{O} \leq 5.5$ V		±10	μΑ
∆ICC	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; \text{ V}_{IH} = V_{CC} - 0.6 \text{ V}$		500	μA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS $t_R = t_F = 2.5ns$; $R_L = 500 \Omega$ (Note 3.)

			Limits			Unit			
				T _A = −40°C to +85°C					
			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \qquad V_{CC} = 2.7 \text{ V} \qquad V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$						
			CL =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	
^t PLH ^t PHL	Propagation Delay Input to Output	1	1.0 1.0	3.6 3.6	1.0 1.0	4.5 4.5	1.0 1.0	4.3 4.3	ns
^t OSHL ^t OSLH	Output-to-Output Skew (Note 4.)			1.0 1.0					ns

3. These AC parameters are preliminary and may be modified.

4. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

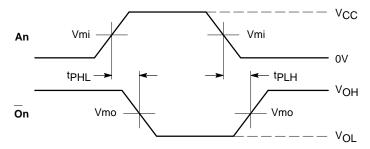
DYNAMIC SWITCHING CHARACTERISTICS

			Т	A = +25°0	C	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
VOLP	Dynamic LOW Peak Voltage (Note 5.)			0.8 0.6		V V
VOLV	Dynamic LOW Valley Voltage (Note 5.)			-0.8 -0.6		V V

5. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

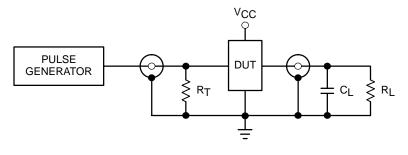
Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	7	pF
COUT	Output Capacitance	V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V _{CC} = 3.3V, V _I = 0V or V _{CC}	25	pF



PROPAGATION DELAYS $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns

	v _{cc}				
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V		
Vmi	1.5 V	1.5 V	V _{CC} /2		
Vmo	1.5 V	1.5 V	V _{CC} /2		

Figure 1. AC Waveforms

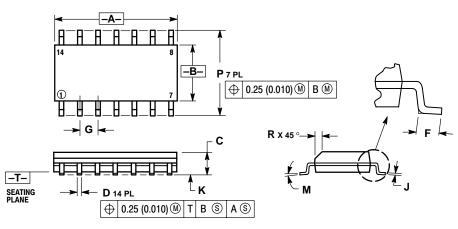


- = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance) = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent (includes jig and probe capacitance) = R₁ = 500 Ω or equivalent = Z_{OUT} of pulse generator (typically 50 Ω) C_L
- CL RL RT

Figure 2. Test Circuit

PACKAGE DIMENSIONS

SO-14 D SUFFIX CASE 751A-03 ISSUE F



NOTES

- DIES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT INVERSE OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

STYLE 4:

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 10. ANODE 11. ANODE 11. ANODE 13. ANODE 14. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE 14. ANODE/CATHODE

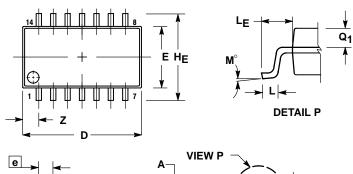
PIN 1.	ANODE/CATHODE
2.	COMMON ANODE
3.	COMMON CATHODE
4.	ANODE/CATHODE
5.	ANODE/CATHODE
6.	ANODE/CATHODE
7.	ANODE/CATHODE
8.	ANODE/CATHODE
9.	ANODE/CATHODE
10.	ANODE/CATHODE
11.	COMMON CATHODE
12.	COMMON ANODE
13.	ANODE/CATHODE
14.	ANODE/CATHODE

TYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE

TYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

PACKAGE DIMENSIONS

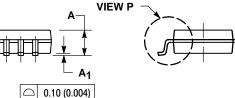
SOIC EIAJ-14 **M SUFFIX** CASE 965-01 ISSUE O



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NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER
- 2. 2. OMMODULE DIMETRICULT MILLINE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q1	0.70	0.90	0.028	0.035
Z		1.42		0.056

TSSOP-14 DT SUFFIX CASE 948G-01 ISSUE O 14X K REF \oplus 0.10 (0.004) M T U S V S ○ 0.15 (0.006) T U ⑤ H П A F H Ν 0.25 (0.010) 2X L/2 B L -U-PIN 1 -IDENT. F DETAIL E ۷ Н Н П 🛆 0.15 (0.006) T U 💲 κ Δ -V-**K1** J J1 SECTION N-N -W-С ☐ 0.10 (0.004) -T- SEATING н DETAIL E D PLANE

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD
- FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- 6.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0°	8 °

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